

ABSTRACT OF THE DISCLOSURE

A pattern formation method of this invention includes the steps of forming a resist film of a chemically amplified resist material and forming a resist pattern by developing the resist film with an alkaline developer after irradiating, through a mask having a desired pattern, the resist film with exposing light having a light component entering the resist film at the Brewster's angle. A thickness reduction ratio of the resist pattern to the resist film is 5% or less.